

ISL9R3060G2, ISL9R3060P2

30A, 600V Stealth™ Diode

General Description

The ISL9R3060G2 and ISL9R3060P2 are Stealth™ diodes optimized for low loss performance in high frequency hard switched applications. The Stealth™ family exhibits low reverse recovery current (I $_{\mbox{\scriptsize RFM}}$) and exceptionally soft recovery under typical operating conditions.

This device is intended for use as a free wheeling or boost diode in power supplies and other power switching applications. The low I_{RBM} and short t_a phase reduce loss in switching transistors. The soft recovery minimizes ringing, expanding the range of conditions under which the diode may be operated without the use of additional snubber circuitry. Consider using the Stealth $^{\rm TM}$ diode with an SMPS IGBT to provide the most efficient and highest power density design at lower cost.

Formerly developmental type TA49411.

Features

•	Soft Recovery $t_b / t_a > 1.2$
•	Fast Recovery t_{rr} < 35ns
•	Operating Temperature 175°C
•	Reverse Voltage
•	Avalanche Energy Rated

Applications

- · Switch Mode Power Supplies
- · Hard Switched PFC Boost Diode
- · UPS Free Wheeling Diode
- · Motor Drive FWD
- SMPS FWD
- · Snubber Diode

Package JEDEC STYLE 2 LEAD TO-247 ANODE CATHODE (BOTTOM SIDE METAL) CATHODE CATHODE CATHODE ANODE CATHODE ANODE CATHODE ANODE

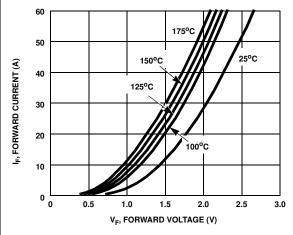
Device Maximum Ratings T_C= 25 ℃ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{RRM}	Peak Repetitive Reverse Voltage	600	V
V _{RWM}	Working Peak Reverse Voltage	600	V
V _R	DC Blocking Voltage	600	V
I _{F(AV)}	Average Rectified Forward Current	30	Α
I _{FRM}	Repetitive Peak Surge Current (20kHz Square Wave)	70	Α
I _{FSM}	Nonrepetitive Peak Surge Current (Halfwave 1 Phase 60Hz)	325	Α
P_{D}	Power Dissipation	200	W
E _{AVL}	Avalanche Energy (1A, 40mH)	20	mJ
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to 175	∞
TL	Maximum Temperature for Soldering		
T_{PKG}	Leads at 0.063in (1.6mm) from Case for 10s	300	℃
	Package Body for 10s, See Techbrief TB334	260	℃

CAUTION: Stresses above those listed in "Device Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

Device	Marking	Device	Package	Tape Width			Quan	tity
R30	60G2	ISL9R3060G2	TO-247	-			-	
R30	60P2	ISL9R3060P2	TO-220AC	-			-	
Electric	cal Cha	racteristics T _C = 2	5°C unless otherwise	noted				
Symbol	Parameter Test Conditions			Min	Тур	Max	Units	
Off State	Characte	eristics						
I _R	Instantaneous Reverse Current		V _R = 600V	T _C = 25 °C	-	-	100	μА
			11	$T_{C} = 25 ^{\circ}C$ $T_{C} = 125 ^{\circ}C$	-	-	1.0	mA
On State	Characte	eristics						
V _F	Instantaneous Forward Voltage	I _F = 30A	T _C = 25 °C	-	2.1	2.4	V	
		· ·	'	T _C = 125℃	-	1.7	2.1	V
Dvnamic	Characte	ristics	<u>.</u>					
C _{.l}		Capacitance	V _R = 10V, I _F = 0)A		120	-	pF
	II	'	• K = 10 • , • F = 0	,,,		120		l b.
Switching	g Charact	eristics						
t _{rr}	Reverse Recovery Time		$I_F = 1A$, $d_{IF}/dt =$	= 100A/μs, V _R = 30V	-	27	35	ns
			$I_F = 30A$, d_{IF}/dt	$I_F = 30A$, $d_{IF}/dt = 100A/\mu s$, $V_R = 30V$		36	45	ns
t _{rr}	Reverse F	Recovery Time	$I_{F} = 30A$,	1		36	-	ns
I_{RRM}	Maximum Reverse Recovery Current d _{IF} /dt = 200A/μs,			-	2.9	-	Α	
Q _{RR}	Reverse F	Recovery Charge	$V_R = 390V, T_C$	V _R = 390V, T _C = 25 °C		55	-	nC
t _{rr}	Reverse F	Recovery Time	I _F = 30A,	I _F = 30A,		110	-	ns
S	Softness F	actor (t _b /t _a)		$d_{IF}/dt = 200A/\mu s$,		1.9	-	
I _{RRM}	Maximum	Maximum Reverse Recovery Current		V _R = 390V, -T _C = 125 <i>°</i> C		6	-	Α
Q _{RR}			1 _C = 125°C			450	-	nC
t _{rr}	Reverse F	Recovery Time	I _F = 30A,	I _F = 30A,		60	-	ns
S	Softness F	actor (t _b /t _a)		d _{IF} /dt = 1000A/μs,			-	
I _{RRM} Maximum Reverse Recovery Current			$V_{R} = 390V,$		21	-	Α	
Q _{RR}	Reverse F	Recovery Charge	T _C = 125 ℃			730	-	nC
dI _M /dt	1	di/dt during t _b		7			-	A/μs
	Characte	rietice	•			•	•	•
Thermal	Ullala	ะแอแนอ						
Thermal	,		se		-	-	0.75	°C/W
Thermal	Thermal R	Resistance Junction to Castesistance Junction to Am			-	-	0.75 30	°C/W

Typical Performance Curves



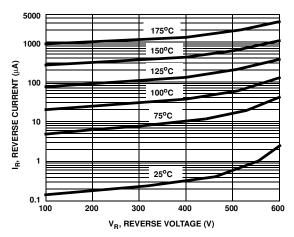
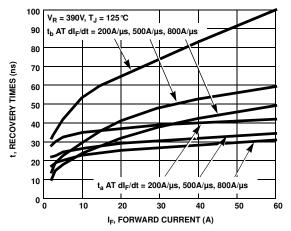


Figure 1. Forward Current vs Forward Voltage

Figure 2. Reverse Current vs Reverse Voltage



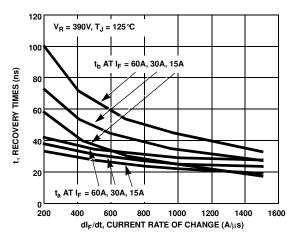
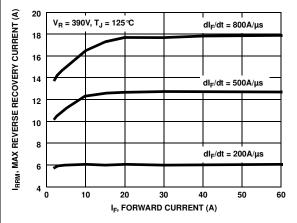


Figure 3. t_a and t_b Curves vs Forward Current

Figure 4. t_a and t_b Curves vs dl_F/dt



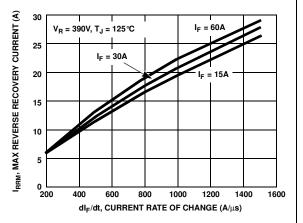
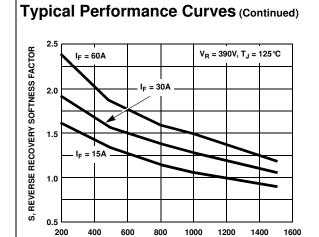


Figure 5. Maximum Reverse Recovery Current vs
Forward Current

Figure 6. Maximum Reverse Recovery Current vs dI_F/dt



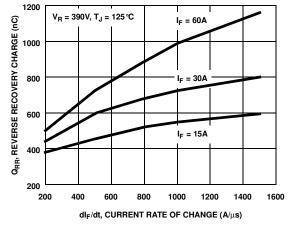
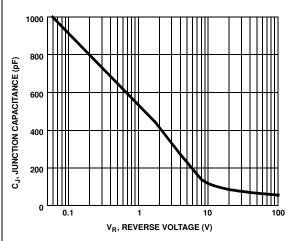


Figure 7. Reverse Recovery Softness Factor vs $\mathrm{dI_F/dt}$

dIF/dt, CURRENT RATE OF CHANGE (A/µs)

Figure 8. Reverse Recovery Charge vs $\mathrm{dI}_{\mathrm{F}}/\mathrm{dt}$



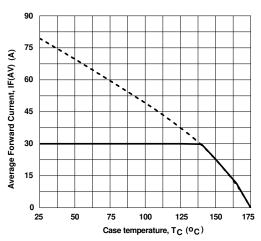


Figure 9. Junction Capacitance vs Reverse Voltage

Figure 10. Forward Current Derating Curve

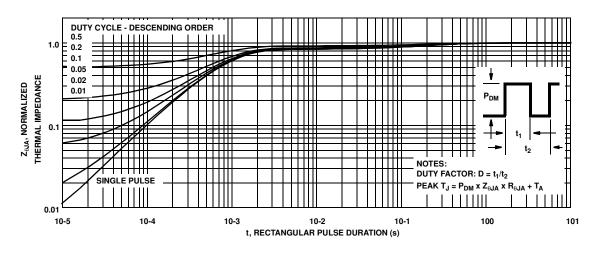
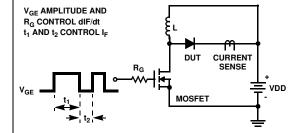


Figure 11. Normalized Maximum Transient Thermal Impedance

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Test Circuit and Waveforms



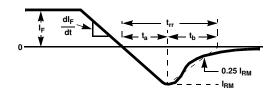


Figure 11. t_{rr} Test Circuit

Figure 12. t_{rr} Waveforms and Definitions

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I = 1A
L = 40mH
R < 0.1\Omega
V_{DD} = 50V
EAVL = 1/2L12 \left[V_{R(AVL)}/(V_{R(AVL)} - V_{DD})\right]
Q1 = IGBT \left(BV_{CES} > DUT V_{R(AVL)}\right)
CURRENT
SENSE
V_{DD}
V_{DD}
DUT
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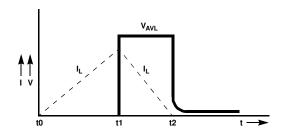


Figure 13. Avalanche Energy Test Circuit

Figure 14. Avalanche Current and Voltage Waveforms





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